

Jun Tatebayashi

List of Publications by Citations

Source: <https://exaly.com/author-pdf/5914428/jun-tatebayashi-publications-by-citations.pdf>

Version: 2024-04-28

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

102
papers

2,014
citations

25
h-index

40
g-index

137
ext. papers

2,287
ext. citations

3
avg, IF

4.46
L-index

#	Paper	IF	Citations
102	Over 1.5 μm light emission from InAs quantum dots embedded in InGaAs strain-reducing layer grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2001 , 78, 3469-3471	3.4	209
101	Room-temperature lasing in a single nanowire with quantum dots. <i>Nature Photonics</i> , 2015 , 9, 501-505	33.9	132
100	Size, shape, and strain dependence of the g factor in self-assembled In(Ga)As quantum dots. <i>Physical Review B</i> , 2004 , 70,	3.3	95
99	III/V ratio based selectivity between strained Stranski-Krastanov and strain-free GaSb quantum dots on GaAs. <i>Applied Physics Letters</i> , 2006 , 89, 161104	3.4	80
98	Low-Threshold near-Infrared GaAs/AlGaAs Core/Shell Nanowire Plasmon Laser. <i>ACS Photonics</i> , 2015 , 2, 165-171	6.3	75
97	A Nanowire-Based Plasmonic Quantum Dot Laser. <i>Nano Letters</i> , 2016 , 16, 2845-50	11.5	53
96	Narrow photoluminescence linewidth (. <i>Applied Physics Letters</i> , 2004 , 84, 2817-2819	3.4	51
95	Formation and optical characteristics of strain-relieved and densely stacked GaSb/InGaAs quantum dots. <i>Applied Physics Letters</i> , 2006 , 89, 203116	3.4	49
94	1.28 μm lasing from stacked InAs/InGaAs quantum dots with low-temperature-grown AlGaAs cladding layer by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2005 , 86, 053107	3.4	48
93	Control of optical polarization anisotropy in edge emitting luminescence of InAs/GaAs self-assembled quantum dots. <i>Applied Physics Letters</i> , 2004 , 84, 1820-1822	3.4	48
92	Lasing characteristics of GaSb/InGaAs self-assembled quantum dots embedded in an InGaAs quantum well. <i>Applied Physics Letters</i> , 2007 , 90, 261115	3.4	45
91	Tuning of g-factor in self-assembled In(Ga)As quantum dots through strain engineering. <i>Physical Review B</i> , 2005 , 71,	3.3	45
90	Controlled InAs quantum dot nucleation on faceted nanopatterned pyramids. <i>Applied Physics Letters</i> , 2007 , 90, 183103	3.4	43
89	InAs/InGaAs self-assembled quantum-dot lasers grown by metalorganic chemical vapor deposition Effects of postgrowth annealing on stacked InAs quantum dots. <i>Applied Physics Letters</i> , 2004 , 85, 1024-1026	3.4	41
88	Site-controlled formation of InAs/GaAs quantum-dot-in-nanowires for single photon emitters. <i>Applied Physics Letters</i> , 2012 , 100, 263101	3.4	40
87	Area-controlled growth of InAs quantum dots and improvement of density and size distribution. <i>Applied Physics Letters</i> , 2000 , 77, 3382-3384	3.4	36
86	Strain compensation technique in self-assembled InAs/GaAs quantum dots for applications to photonic devices. <i>Journal Physics D: Applied Physics</i> , 2009 , 42, 073002	3	35

85	Room temperature continuous wave lasing in InAs quantum-dot microdisks with air cladding. <i>Optics Express</i> , 2005 , 13, 1615-20	3.3	35
84	Low threshold current operation of self-assembled InAs/GaAs quantum dot lasers by metal organic chemical vapour deposition. <i>Electronics Letters</i> , 2003 , 39, 1130	1.1	35
83	GaSb/GaAs type-II quantum dots grown by droplet epitaxy. <i>Nanotechnology</i> , 2009 , 20, 455604	3.4	34
82	Complex emission dynamics of type-II GaSb/GaAs quantum dots. <i>Applied Physics Letters</i> , 2009 , 95, 061103	3.4	33
81	Coulomb-induced emission dynamics and self-consistent calculations of type-II Sb-containing quantum dot systems. <i>Physical Review B</i> , 2012 , 85,	3.3	26
80	1.54 [micro sign]m GaSb/AlGaSb multi-quantum-well monolithic laser at 77 K grown on miscut Si substrate using interfacial misfit arrays. <i>Electronics Letters</i> , 2007 , 43, 1198	1.1	26
79	Lasing characteristics of InAs quantum-dot microdisk from 3K to room temperature. <i>Applied Physics Letters</i> , 2004 , 85, 1326-1328	3.4	26
78	Single dot spectroscopy of site-controlled InAs quantum dots nucleated on GaAs nanopyramids. <i>Applied Physics Letters</i> , 2007 , 91, 133104	3.4	25
77	Room-Temperature Operation of Buffer-Free GaSb/AlGaSb Quantum-Well Diode Lasers Grown on a GaAs Platform Emitting at 1.65 μm . <i>IEEE Photonics Technology Letters</i> , 2007 , 19, 1628-1630	2.2	23
76	Circular dichroism in a three-dimensional semiconductor chiral photonic crystal. <i>Applied Physics Letters</i> , 2014 , 105, 051107	3.4	22
75	Time-resolved photoluminescence of type-II Ga(As)Sb/GaAs quantum dots embedded in an InGaAs quantum well. <i>Nanotechnology</i> , 2008 , 19, 295704	3.4	21
74	Effects of rapid thermal annealing on the emission properties of highly uniform self-assembled InAs/GaAs quantum dots emitting at 1.3 μm . <i>Applied Physics Letters</i> , 2007 , 90, 111912	3.4	21
73	Luminescence in excess of 1.5 μm at room-temperature of InAs quantum dots capped by a thin InGaAs strain-reducing layer. <i>Journal of Crystal Growth</i> , 2002 , 237-239, 1296-1300	1.6	21
72	Highly uniform, multi-stacked InGaAs/GaAs quantum dots embedded in a GaAs nanowire. <i>Applied Physics Letters</i> , 2014 , 105, 103104	3.4	20
71	Lateral interdot carrier transfer in an InAs quantum dot cluster grown on a pyramidal GaAs surface. <i>Nanotechnology</i> , 2011 , 22, 055706	3.4	20
70	Monolithically Integrated III-Sb-Based Laser Diodes Grown on Miscut Si Substrates. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2009 , 15, 716-723	3.8	19
69	Coulomb effects in type-II Ga(As)Sb quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , 2009 , 246, 752-755	1.3	19
68	Formation of ultrahigh-density InAs/AlAs quantum dots by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2004 , 84, 1877-1879	3.4	19

- 67 Localized strain reduction in strain-compensated InAs/GaAs stacked quantum dot structures. *Applied Physics Letters*, **2007**, 90, 163121 3-4 18
- 66 Room-temperature lasing at 1.82 μm of GaInSb/AlGaSb quantum wells grown on GaAs substrates using an interfacial misfit array. *Applied Physics Letters*, **2007**, 91, 141102 3-4 18
- 65 Ground-state lasing of stacked InAs/GaAs quantum dots with GaP strain-compensation layers grown by metal organic chemical vapor deposition. *Applied Physics Letters*, **2006**, 88, 221107 3-4 18
- 64 Improvement of the uniformity of self-assembled InAs quantum dots grown on InGaAs/GaAs by low-pressure metalorganic chemical vapor deposition. *Applied Physics Letters*, **2004**, 85, 2753-2755 3-4 18
- 63 Giant optical rotation in a three-dimensional semiconductor chiral photonic crystal. *Optics Express*, **2013**, 21, 29905-13 3-3 17
- 62 Visible light emission from self-catalyzed GaInP/GaP core-shell double heterostructure nanowires on silicon. *Journal of Applied Physics*, **2010**, 108, 034315 2-5 17
- 61 Improved photoluminescence efficiency of patterned quantum dots incorporating a dots-in-the-well structure. *Nanotechnology*, **2008**, 19, 435710 3-4 16
- 60 Optical properties of patterned InAs quantum dot ensembles grown on GaAs nanopramids. *Applied Physics Letters*, **2007**, 91, 243106 3-4 16
- 59 Carrier relaxation in closely stacked InAs quantum dots. *Journal of Applied Physics*, **2004**, 96, 150-154 2-5 16
- 58 Lasing at 1.28 μm of InAs-GaAs quantum dots with AlGaAs cladding layer grown by metal-organic chemical vapor deposition. *IEEE Journal of Selected Topics in Quantum Electronics*, **2005**, 11, 1027-1034 3-8 15
- 57 Eu-doped GaN and InGaN monolithically stacked full-color LEDs with a wide color gamut. *Applied Physics Express*, **2021**, 14, 031008 2-4 15
- 56 Optical transition pathways in type-II Ga(As)Sb quantum dots. *Journal of Luminescence*, **2009**, 129, 456-460 3-8 14
- 55 Excitation Efficiency and Limitations of the Luminescence of Eu³⁺ Ions in GaN. *Physical Review Applied*, **2020**, 13, 033102 4-3 13
- 54 Fabrication and characteristics of broad-area light-emitting diode based on nanopatterned quantum dots. *Nanotechnology*, **2009**, 20, 035302 3-4 13
- 53 Development of Electrically Driven Single-Quantum-Dot Device at Optical Fiber Bands. *Japanese Journal of Applied Physics*, **2006**, 45, 3621-3624 1-4 12
- 52 Growth of InGaAs/GaAs nanowire-quantum dots on AlGaAs/GaAs distributed Bragg reflectors for laser applications. *Journal of Crystal Growth*, **2017**, 468, 144-148 1-6 10
- 51 Improved surface morphology of stacked 1.3 μm InAs/GaAs quantum dot active regions by introducing annealing processes. *Applied Physics Letters*, **2006**, 89, 081902 3-4 10
- 50 Color-Tunability in GaN LEDs Based on Atomic Emission Manipulation under Current Injection. *ACS Photonics*, **2019**, 6, 1153-1161 6-3 9

49	GaN:Eu,O-Based Resonant-Cavity Light Emitting Diodes with Conductive AlInN/GaN Distributed Bragg Reflectors. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 732-738	4	9
48	Optical characteristics of GaInP/GaP double-heterostructure core-shell nanowires embedded in polydimethylsiloxane membranes. <i>Applied Physics Letters</i> , 2010 , 96, 253101	3-4	9
47	Effects of accumulated strain on the surface and optical properties of stacked 1.3 μ m InAs/GaAs quantum dot structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008 , 40, 2182-2184	3	9
46	Demonstration of a three-dimensional photonic crystal nanocavity in a <110>-layered diamond structure. <i>Applied Physics Letters</i> , 2015 , 107, 071102	3-4	8
45	Controlled Formation and Dynamic Wulff Simulation of Equilibrium Crystal Shapes of GaAs Pyramidal Structures on Nanopatterned Substrates. <i>Crystal Growth and Design</i> , 2010 , 10, 2509-2514	3-5	8
44	Continuous-Wave, Room-Temperature Operation of 2- μ m Sb-Based Optically-Pumped Vertical-External-Cavity Surface-Emitting Laser Monolithically Grown on GaAs Substrates. <i>Applied Physics Express</i> , 2009 , 2, 112102	2-4	8
43	Observation of 1.55 μ m Light Emission from InAs Quantum Dots in Photonic Crystal Microcavity. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 2579-2583	1-4	8
42	Circularly polarized vacuum field in three-dimensional chiral photonic crystals probed by quantum dot emission. <i>Physical Review B</i> , 2017 , 96,	3-3	7
41	Formation and Optical Characteristics of Type-II Strain-Relieved GaSb/GaAs Quantum Dots by Using an Interfacial Misfit Growth Mode. <i>IEEE Nanotechnology Magazine</i> , 2009 , 8, 269-274	2-6	7
40	Structural and optical properties of high-density (>10 ¹¹ /cm ²) InAs QDs with varying Al(Ga)As matrix layer thickness. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 21, 279-284	3	6
39	Purcell-Effect-Enhanced Radiative Rate of Eu ³⁺ Ions in GaN Microdisks. <i>Physical Review Applied</i> , 2020 , 14,	4-3	6
38	Room-temperature operation of near-infrared light-emitting diode based on Tm-doped GaN with ultra-stable emission wavelength. <i>Journal of Applied Physics</i> , 2020 , 127, 113103	2-5	5
37	Control of the energy transfer between Tm ³⁺ and Yb ³⁺ ions in Tm,Yb-codoped ZnO grown by sputtering-assisted metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2018 , 123, 161409	3-5	5
36	Formation and optical properties of Tm,Yb-codoped ZnO nanowires grown by sputtering-assisted metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2018 , 503, 13-19	1-6	5
35	Quantitative study of energy-transfer mechanism in Eu,O-codoped GaN by time-resolved photoluminescence spectroscopy. <i>Journal of Applied Physics</i> , 2018 , 123, 161419	2-5	4
34	Localized-surface-plasmon-enhanced GaN:Eu-based red light-emitting diodes utilizing silver nanoparticles. <i>Applied Physics Express</i> , 2019 , 12, 095003	2-4	4
33	Formation and optical properties of multi-stack InGaAs quantum dots embedded in GaAs nanowires by selective metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2013 , 370, 299-302	1-6	4
32	1.52 μ m photoluminescence emissions from InAs quantum dots grown on nanopatterned GaAs buffers. <i>Applied Physics Letters</i> , 2010 , 97, 143111	3-4	4

31	Optical Characteristics of Two-Dimensional Photonic Crystal Slab Nanocavities with Self-Assembled InAs Quantum Dots for 1.3 μm Light Emission. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, 2391-2394	1.4	4
30	Enhanced Optical Properties of High-Density ($>10^{11}/\text{cm}^2$) InAs/AlAs Quantum Dots by Hydrogen Passivation. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, 2118-2121	1.4	4
29	Area-Controlled Growth of InAs Quantum Dots by Selective MOCVD. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, 2344-2346	1.4	4
28	Direct detection of rare earth ion distributions in gallium nitride and its influence on growth morphology. <i>Journal of Applied Physics</i> , 2020 , 127, 013102	2.5	4
27	Growth and optical characteristics of Tm-doped AlGaIn layer grown by organometallic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2018 , 123, 161406	2.5	3
26	Picosecond time-resolved dynamics of energy transfer between GaN and the various excited states of Eu^{3+} ions. <i>Physical Review B</i> , 2019 , 100,	3.3	3
25	Electric field modulation of exciton recombination in InAs/GaAs quantum dots emitting at 1.3 μm . <i>Journal of Applied Physics</i> , 2008 , 104, 013504	2.5	3
24	Device Characteristics of GaInSb/AlGaSb Quantum Well Lasers Monolithically Grown on GaAs Substrates by Using an Interfacial Misfit Array. <i>Journal of Electronic Materials</i> , 2008 , 37, 1758-1763	1.9	3
23	Measurement of electro-optic coefficients of 1.3 [μm] self-assembled InAs/GaAs quantum dots. <i>Electronics Letters</i> , 2007 , 43, 410	1.1	3
22	Spectroscopy on single columns of vertically aligned InAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 21, 409-413	3	3
21	InAs/AlAs quantum dots with InGaAs insertion layer: dependence of the indium composition and the thickness. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005 , 26, 138-142	3	3
20	Enhanced Red Emission of Eu, O-Codoped GaN Embedded in a Photonic Crystal Nanocavity with Hexagonal Air Holes. <i>Physical Review Applied</i> , 2021 , 15,	4.3	3
19	Nanowire quantum-dot lasers on flexible membranes. <i>Applied Physics Express</i> , 2018 , 11, 065002	2.4	3
18	Numerical analysis of DFB lasing action in photonic crystals with quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 21, 814-819	3	2
17	Highly uniform self-assembled InAs/GaAs quantum dots emitting at 1.3 μm by metalorganic chemical vapor deposition. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005 , 26, 77-80	3	2
16	Growth area control of InAs quantum dots for photonic-crystal-based optical devices by selective MOCVD 2001 ,		2
15	Droop-free amplified red emission from Eu ions in GaN. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, 120905	1.4	2
14	Optical Properties of Site-Controlled InGaAs Quantum Dots Embedded in GaAs Nanowires by Selective Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 11PE13	1.4	2

13	Enhanced luminescence efficiency of GaN:Eu-based light-emitting diodes by localized surface plasmons utilizing gold nanoparticles. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SCCC09	1.4	1
12	Room-temperature lasing in GaAs nanowires embedding multi-stacked InGaAs/GaAs quantum dots 2015 ,		1
11	Modeling defect mediated color-tunability in LEDs with Eu-doped GaN-based active layers. <i>Journal of Applied Physics</i> , 2022 , 131, 045701	2.5	1
10	Quantitative evaluation of enhanced Er luminescence in GaAs-based two-dimensional photonic crystal nanocavities. <i>Applied Physics Letters</i> , 2020 , 116, 181102	3.4	1
9	Formation and optical characteristics of ZnO:Eu/ZnO nanowires grown by sputtering-assisted metalorganic chemical vapor deposition. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, SCCE05	1.4	1
8	Elucidation of the excitation mechanism of Tb ions doped in Al _x Ga _{1-x} N grown by OMVPE toward a wavelength-stable green emitter. <i>Journal of Applied Physics</i> , 2022 , 131, 073102	2.5	1
7	Investigation on Suitable Structure for Laser Oscillation in Eu-doped GaN with Two-Dimensional Photonic Crystal Nanocavities. <i>Zairyo/Journal of the Society of Materials Science, Japan</i> , 2020 , 69, 721-726	0.1	0
6	16.3: Invited Paper: New development in Red Light-emitting Diodes (LEDs) using Eu-doped GaN for Monolithic Micro-LED Displays. <i>Digest of Technical Papers SID International Symposium</i> , 2019 , 50, 167-167	0.5	
5	Enhancement of Er luminescence in microdisk resonators made of Er,O-codoped GaAs. <i>Journal of Applied Physics</i> , 2020 , 127, 233101	2.5	
4	Formation of a single In(Ga)As/GaAs quantum dot embedded in a site-controlled GaAs nanowire by metalorganic chemical vapor deposition for application to single photon sources. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1439, 115-119		
3	Perspective of Semiconductor Technologies Contributed to the IoT Society. <i>Zairyo/Journal of the Society of Materials Science, Japan</i> , 2020 , 69, 762-766	0.1	
2	Enhanced Photoluminescence in High-Q Photonic Crystal Nanocavities with Er,O-Codoped GaAs. <i>Zairyo/Journal of the Society of Materials Science, Japan</i> , 2020 , 69, 823-828	0.1	
1	47-3: Invited Paper: High Brightness and RGB Integration of Eu-doped GaN-based Red LEDs for Ultrahigh-resolution Micro-LED Display. <i>Digest of Technical Papers SID International Symposium</i> , 2020 , 51, 691-694	0.5	